

## **Product / Process Change Notice**

**Parts Affected:**

Chip process CP547, PNP silicon, Darlington power transistor wafers, and bare die.

**Extent of Change:**

The CP547 wafer process has been discontinued and replaced with the CP647 wafer process.

The overall wafer diameter is being reduced from 5 inch to 4 inch.

The die size and pattern has been changed; see figures 1 and 2 for details.

**Reason for Change:**

This process was transferred to an alternate wafer foundry due to low volume production.

**Effect of Change:**

The wafer process meets all electrical specifications of the individual devices listed on the following page.

**Qualification:**

Standard evaluation and qualifications completed resulting in no performance degradation.

**Effective Date of Change:**

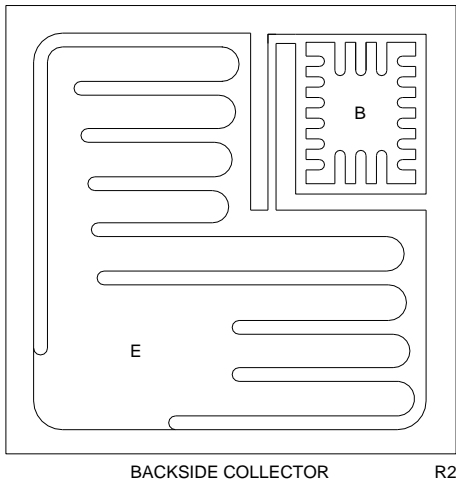
May 4, 2015 - Existing inventory will be shipped until depleted.

**Sample Availability:**

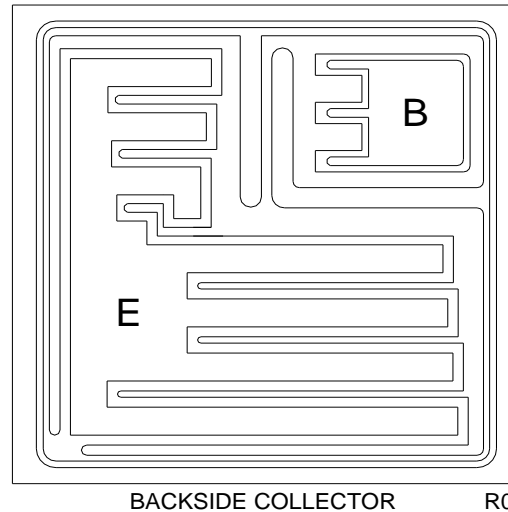
Please contact Salesperson or Manufacturer's Representative.

**Figures:**

**Figure 1: CP547 Chip Geometry (Discontinued)**



**Figure 2: CP647 Chip Geometry**



Wafer Diameter: 5 inch  
Die Size: 195 x 195 mils  
Die Thickness: 11.4 mils  
Bond Pad Size (Emitter): 61 x 35 mils  
Bond Pad Size (Base): 29 x 29 mils  
Topside Metal: Al (60,000Å)  
Backside Metal: Ti/Ni/Au (1,100Å/4,000Å/500Å)

Wafer Diameter: 4 inch  
Die Size: 211 x 211 mils  
Die Thickness: 12.5 mils  
Bond Pad Size (Emitter): 60 x 50 mils  
Bond Pad Size (Base): 49 x 41 mils  
Topside Metal: Al (50,000Å)  
Backside Metal: Ti/Ni/Ag (1,000Å/6,000Å/10,000Å)

**Part Numbers Affected**

- CP547-CEN1103-CT
- CP547-MJ11013-CT
- CP547-MJ11015-CT
- CP547-MJ11015-WN
- CP547-PMD19K100-CT
- CP547-PMD19K100-WN
- CP547-2N6287-CT